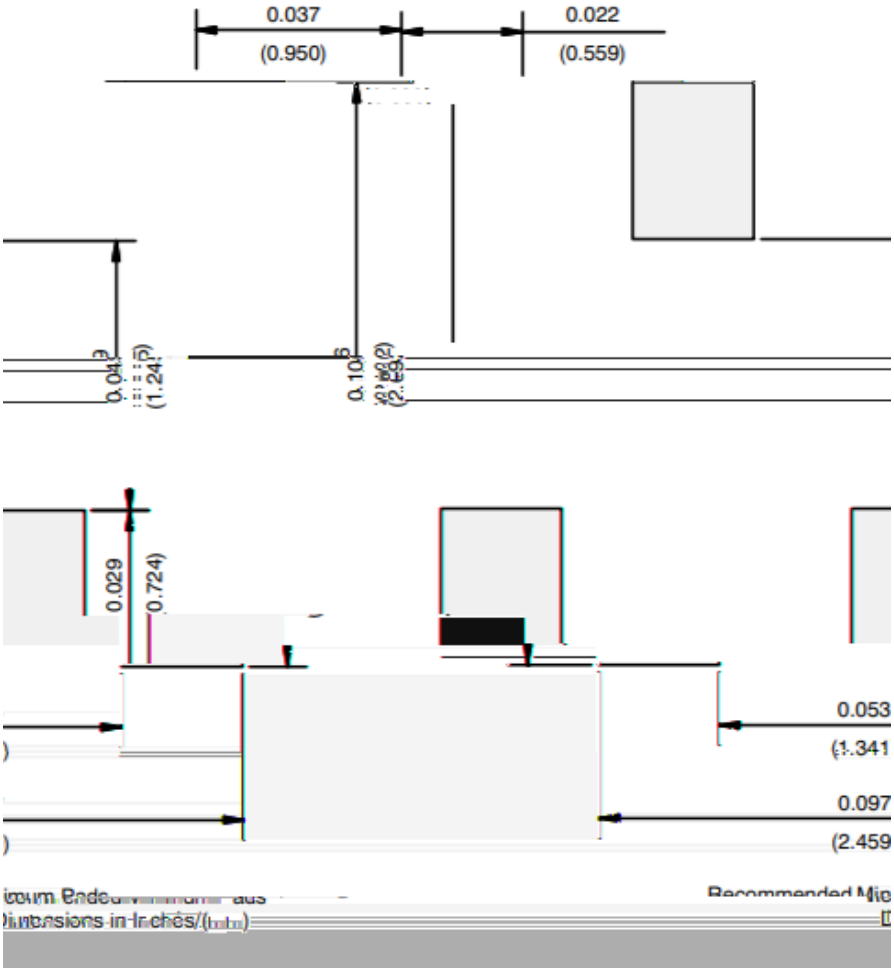
20V N-Channel Enhancement Mode MOSFET

The JXP2300VRG uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and high density cell Design for ultra low on-resistance. This device is suitable for use as

Parameter		Symbol	Typ	Max	Unit
Maximum junction-to-ambient [a]		R	120	145	/W
	Steady-State		140	175	
Maximum junction-to-foot	Steady-State	R	62	78	

Notes


0.037
(0.950)
0.022
(0.559)
0.029
(0.724)
0.053
0.097
(2.459